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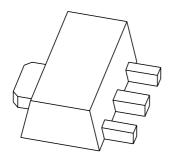
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BCV28; BCV48 PNP Darlington transistors

Product data sheet Supersedes data of 1999 Apr 08

2004 Dec 06



PNP Darlington transistors

BCV28; **BCV48**

FEATURES

- Very high DC current gain (min. 10000)
- High current (max. 500 mA)
- Low voltage (max. 60 V).

APPLICATIONS

· Where very high amplification is required.

DESCRIPTION

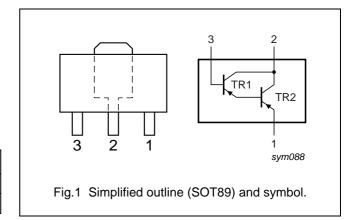
PNP Darlington transistor in a SOT89 plastic package. NPN complements: BCV29 and BCV49.

MARKING

TYPE NUMBER	MARKING CODE
BCV28	ED
BCV48	EE

PINNING

PIN	DESCRIPTION	
1	emitter	
2	collector	
3	base	



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
TIPE NUMBER	NAME DESCRIPTION		VERSION
BCV28	SC-62	plastic surface mounted package; collector pad for good heat	SOT89
BCV48		transfer; 3 leads	

PNP Darlington transistors

BCV28; BCV48

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCV28		_	-40	V
	BCV48		_	-80	V
V _{CES}	collector-emitter voltage	V _{BE} = 0 V			
	BCV28		_	-30	V
	BCV48		_	-60	V
V _{EBO}	emitter-base voltage	open collector	_	-10	V
I _C	collector current (DC)		_	-500	mA
I _{CM}	peak collector current		_	-800	mA
I _B	base current (DC)		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	1.3	W
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	96	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point		16	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm². For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

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PNP Darlington transistors

BCV28; BCV48

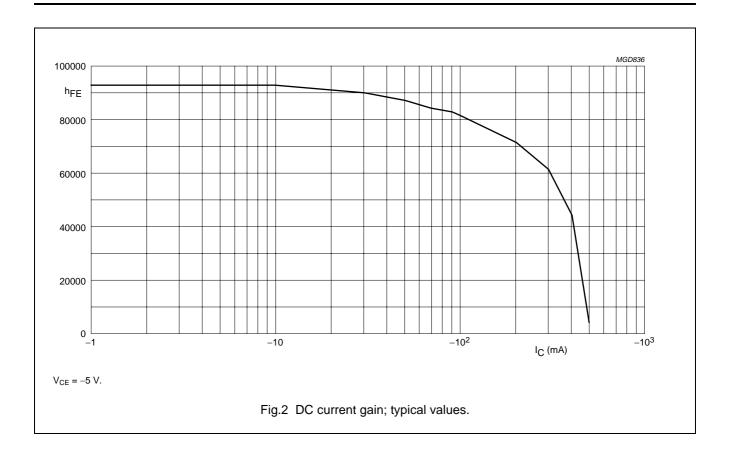
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current					
	BCV28	$I_E = 0 \text{ A}; V_{CB} = -30 \text{ V}$	_	_	-100	nA
	BCV48	$I_E = 0 \text{ A}; V_{CB} = -60 \text{ V}$	_	_	-100	nA
I _{EBO}	emitter-base cut-off current	$I_C = 0 \text{ A}; V_{BE} = -10 \text{ V}$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -5 \text{ V}; \text{ see Fig.2}$				
	BCV28		4000	_	_	
	BCV48		2000	_	_	
	DC current gain	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}; \text{ see Fig.2}$				
	BCV28		10000	_	_	
	BCV48		4000	_	_	
	DC current gain	$I_C = -100 \text{ mA}$; $V_{CE} = -5 \text{ V}$; see Fig.2				
	BCV28		20000	_	_	
	BCV48		10000	_	_	
	DC current gain	$I_C = -500 \text{ mA}$; $V_{CE} = -5 \text{ V}$; see Fig.2				
	BCV28		4000	_	_	
	BCV48		2000	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -100 \text{ mA}; I_B = -0.1 \text{ mA}$	_	_	-1	V
V _{BEsat}	base-emitter saturation voltage	$I_C = -100 \text{ mA}; I_B = -0.1 \text{ mA}$	_	_	-1.5	V
V_{BEon}	base-emitter on-state voltage	$I_C = -10 \text{ mA}; I_B = -5 \text{ mA}$	-	_	-1.4	V
f _T	transition frequency	$I_C = -30 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	_	220	_	MHz

PNP Darlington transistors

BCV28; BCV48



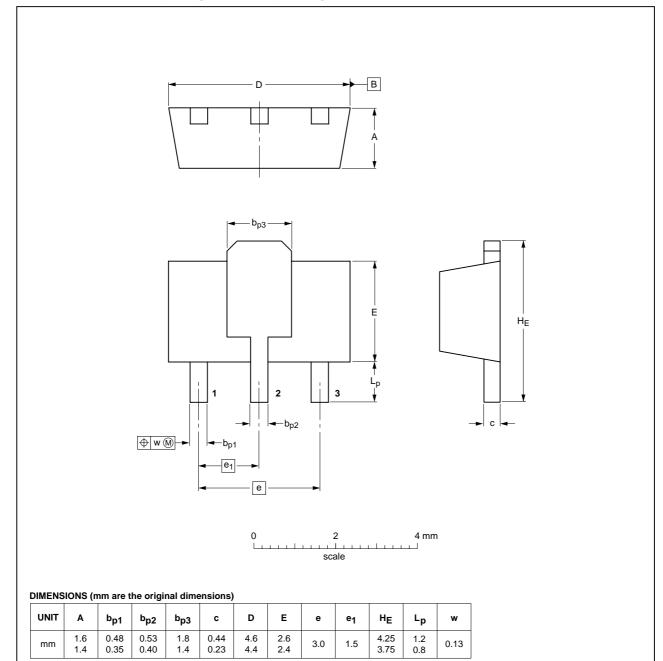
PNP Darlington transistors

BCV28; BCV48

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE	OUTLINE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT89		TO-243	SC-62			04-08-03 06-03-16

2004 Dec 06 6

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PNP Darlington transistors

BCV28; BCV48

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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